

The optimizing mobility-stability trade-off by vertically stacked IGZO/GZO TFT with controlling of Indium-free GZO layer via PEALD

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Supplemental Document

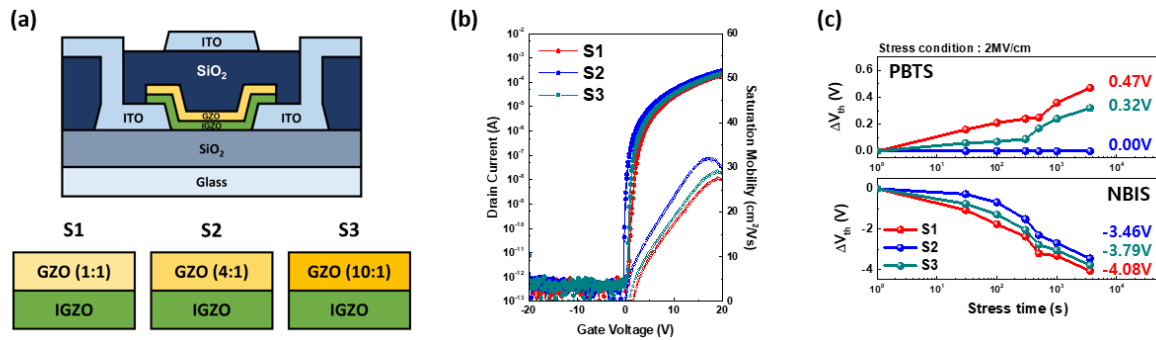


Figure 1. Schematics of (a) the IGZO/GZO TFT structure and cation composition condition of GaZnO layer using PEALD subcycle ratio. (b) The transfer curve of the IGZO/GZO TFTs. (c) Variation of V_{th} for IGZO/GZO TFTs as a function of the PBTS and NBIS time